CMLDM7120TG

SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET

PICOmini™

SOT-563 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM7120TG is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(ON)}$ and a MAX Threshold Voltage of 0.85V.

MARKING CODE: CT7

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

FEATURES:

- Device is ***Halogen Free*** by design
- ESD protection up to 2kV
- Low $r_{DS(ON)}$ (0.25Ω MAX @ V_{GS}=1.5V)
- MAX Threshold Voltage (0.85V)
- Logic level compatibility

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	8.0	V
Continuous Drain Current (Steady State)	I_D	1.0	A
Maximum Pulsed Drain Current, tp=10μs	I_{DM}	4.0	A
Power Dissipation (Note 1)	P_D	350	mW
Power Dissipation (Note 2)	P_D	300	mW
Power Dissipation (Note 3)	P_D	150	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{GSSF}, I_{GSSR}	V_{GS}=8.0V, V_{DS}=0			10	μA
I_{DSS}	V_{DS}=20V, V_{GS}=0			10	μA
BV_{DSS}	V_{GS}=0, I_D=250μA	20			V
$V_{GS(th)}$	V_{DS}=10V, I_D=1.0mA	0.5		0.85	V
V_{SD}	V_{GS}=0, I_S=1.0A			1.10	V
$r_{DS(ON)}$	V_{GS}=4.5V, I_D=0.5A		0.075	0.10	Ω
$r_{DS(ON)}$	V_{GS}=2.5V, I_D=0.5A		0.10	0.14	Ω
$r_{DS(ON)}$	V_{GS}=1.5V, I_D=0.1A		0.20	0.25	Ω
$r_{DS(ON)}$	V_{GS}=1.2V, I_D=0.1A		0.80		Ω
$Q_{g(tot)}$	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		2.4		nC
Q_{gs}	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		0.25		nC
Q_{gd}	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		0.65		nC
g_{FS}	V_{DS}=10V, I_D=0.5A		2.5		S
C_{rss}	V_{DS}=10V, V_{GS}=0, f=1.0MHz		45		pF
C_{iss}	V_{DS}=10V, V_{GS}=0, f=1.0MHz		220		pF
C_{oss}	V_{DS}=10V, V_{GS}=0, f=1.0MHz		120		pF
t_{on}	V_{DD}=10V, V_{GS}=5.0V, I_D=0.5A		25		ns
t_{off}	V_{DD}=10V, V_{GS}=5.0V, I_D=0.5A		140		ns

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm^2
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm^2
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm^2

R2 (2-August 2011)

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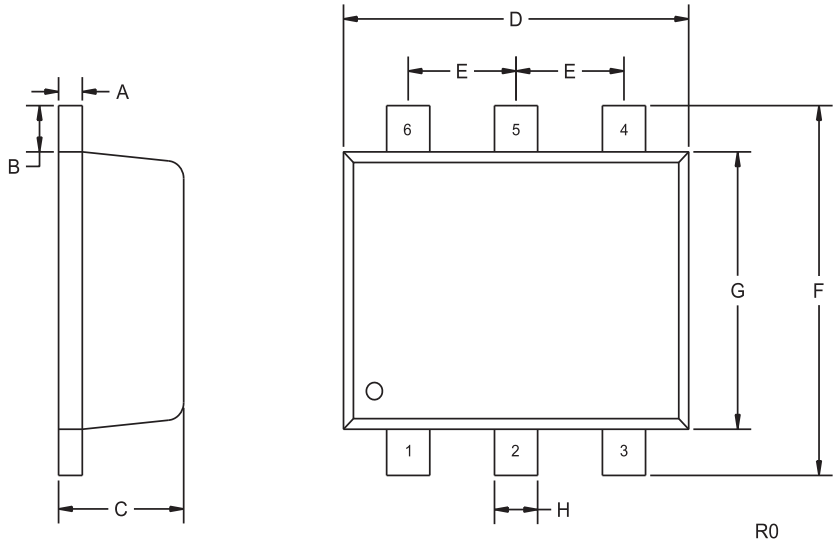
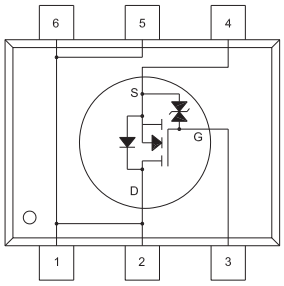
SOT-563 CASE - MECHANICAL OUTLINE



R0

PIN CONFIGURATION



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:
1) Drain
2) Drain
3) Gate
4) Source
5) Drain
6) Drain

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